

FORM PTO-1449 (SUBSTITUTE)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEINFORMATION DISCLOSURE
STATEMENT BY APPLICANT
(37 CFR 1.98(b))Attorney Docket No.: GR99P3456
Appl. No.

Applicant HARALD KUHN ET AL.

Filing Date January 7, 2002
Group Art UnitJc932 U.S. PTO
10/04/2002
01/07/02

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
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FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
<i>MAA</i>	J ✓	32 30 727 A1	2/23/84	Germany			
<i>MAA</i>	K ✓	32 30 727 C2	2/23/84	Germany			
<i>MAA</i>	L ✓	0 389 533 B1	10/3/90	Europe			
<i>MAA</i>	M ✓	09 142 995 A	6/3/97	Japan			
<i>MAA</i>	N ✓	10 182 296 A	7/7/98	Japan			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

<i>MAA</i>	✓	Yoo, W. et al.: "Bulk Crystal Growth of 6H-SiC on Polytype-Controlled Substrates Through Vapor Phase and Characterization", Elsevier Science Publishers B.V., 1991, pp. 733-739; <i>no month</i>
<i>MAA</i>	✓	Takahashi, J. et al.: "Influence of the Seed Face Polarity on the Sublimation Growth of α -SiC", Jpn. J. Appl. Phys., Vol. 34, Part 1, No. 9A, September 1995, pp. 4694-4698; <i>no month</i>

EXAMINER:

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10/29/03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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MAA	J ✓	11 060 390	3/2/99	Japan			
	K						
	L						
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

MAA	Jayathirtha, H. et al.: "Improvement in the Growth Rate of Cubic Silicon Carbide Bulk Single Crystals grown by the sublimation Method", Elsevier Science B.V., 1997, pp. 662-668; <i>no note</i>
MAA	Ohtani, N. et al.: "Development of Large Single-Crystal SiC Substrates", Scripta Technica, 1998, pp. 8-17; <i>no note</i>

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